



HIGH POWER PULSED LASER DIODES



HPL - series of pulsed laser diodes are MQW structure devices with InGaAsP active layers fabricated using advanced MOCVD epitaxial growth techniques. Devices are designed with pulse width FWHM of 50~100ns and repetition frequency up to 15 KHz. Standard TO9mm package with wavelengths of 905 and 1550 nm, different emitter sizes and stack layers are available for various applications such as range finder and optical measurement.

Feature:

- High peak output Power: >50W
- InGaAsP/InGaAsP MQW Structure by MOCVD

Maximum Rating:

Peak Reverse Voltage: V_{rm} 2V

Case Temperature:

Operating -55°C to $+65^{\circ}\text{C}$

Storage -55°C to $+85^{\circ}\text{C}$

Soldering 5 seconds, $+200^{\circ}\text{C}$

Type	RLT-HPL905-50	Unit
Centre Wavelength	905	Nm
Wavelength Range	+/-10	Nm
Peak Forward Current	50	A
Peak Output Power	50	W
Pulse Width Max.	50~100	Ns
Duty Factor	0.05	%
Peak Forward Voltage	50	V
Beam Divergence FWHM	10x40	Degree
Source Size	400x6	μm
Number of Diode Element	3	
Package	TO 9mm package	



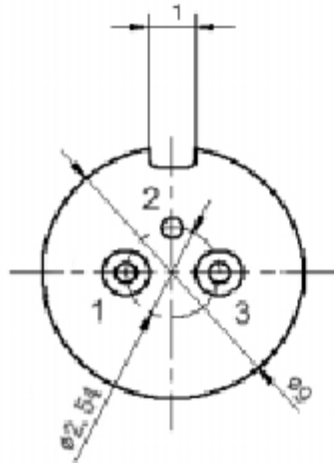
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TO $\Phi 9$ mm Package



1 is LD cathode; 2 is PD anode, 3 is PD cathode

